



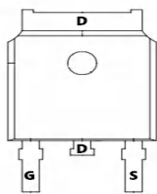
TM40N02D

N-Channel Enhancement Mosfet

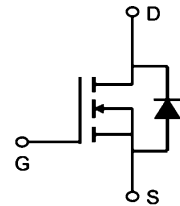
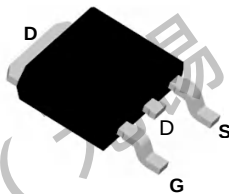
General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features $V_{DS} = 20V$ $I_D = 40A$ $R_{DS(ON)} = 7.5m\Omega (typ.) @ V_{GS} = 4.5V$ 100% UIS Tested 100% R_g Tested
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D:TO-252-3L



Marking: 40N02



Absolute Maximum Ratings ($T_C = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	40	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	20	A
I_{DM}	Pulsed Drain Current	78	A
EAS	Single Pulse Avalanche Energy	23	mJ
I_{AS}	Avalanche Current	21	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	15	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	6.6	$^\circ C/W$



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Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.7	0.9	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =4.5V, I _D =15A	-	7.5	11	mΩ
		V _{GS} =2.5V, I _D =10A	-	11	17.5	
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	860	-	pF
C _{oSS}	Output Capacitance		-	182	-	pF
C _{rSS}	Reverse Transfer Capacitance		-	164	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =15A, V _{GS} =4.5V	-	15	-	nC
Q _{gs}	Gate-Source Charge		-	2	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	5.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, I _D =15A, R _{GEN} =3Ω, V _{GS} =4.5V	-	9	-	ns
t _r	Turn-on Rise Time		-	25	-	ns
t _{d(off)}	Turn-off Delay Time		-	37	-	ns
t _f	Turn-off Fall Time		-	14	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _s	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	120	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V



Typical Performance Characteristics

Figure 1: Output Characteristics

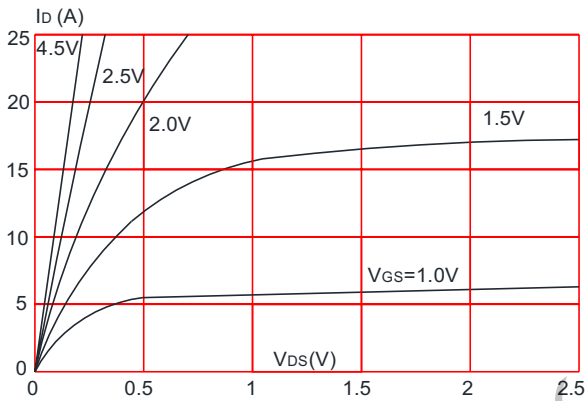


Figure 2: Typical Transfer Characteristics

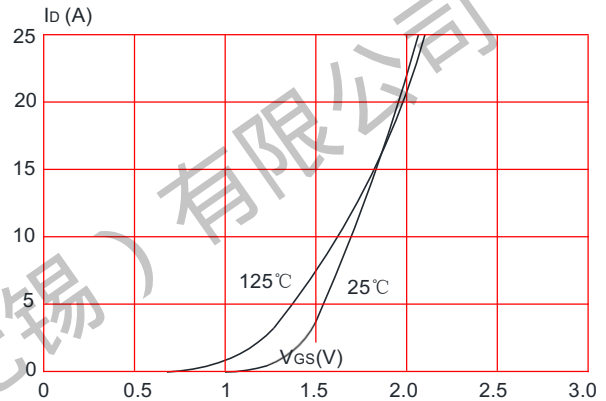


Figure 3: On-resistance vs. Drain Current

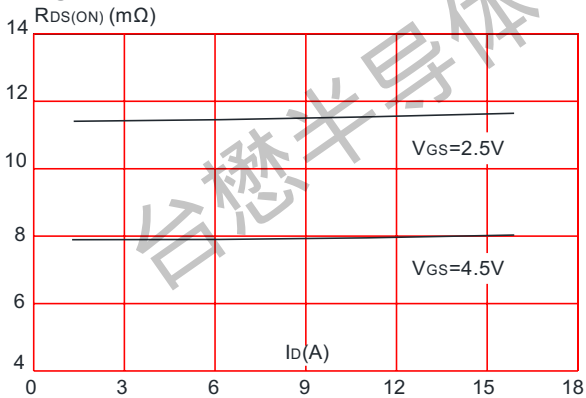


Figure 4: Body Diode Characteristics

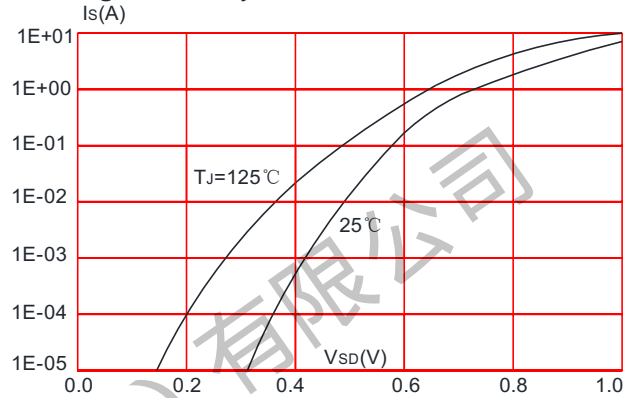


Figure 5: Gate Charge Characteristics

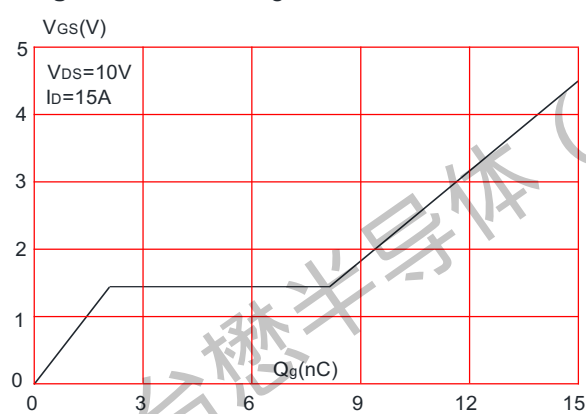
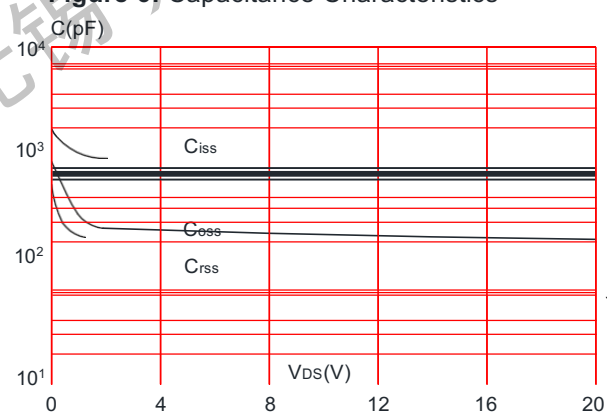


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

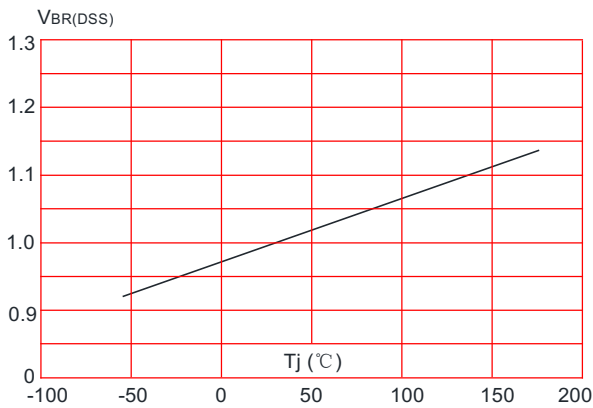


Figure 8: Normalized on Resistance vs. Junction Temperature

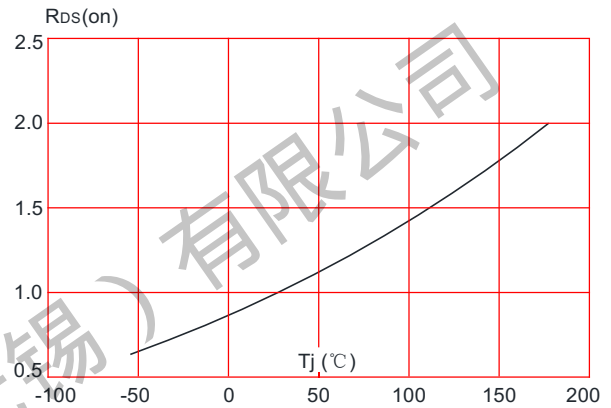


Figure 9: Maximum Safe Operating Area

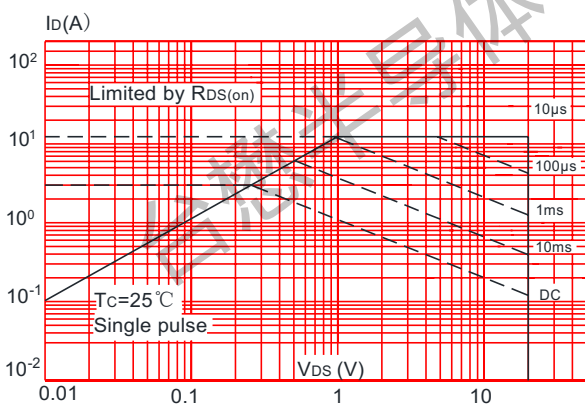
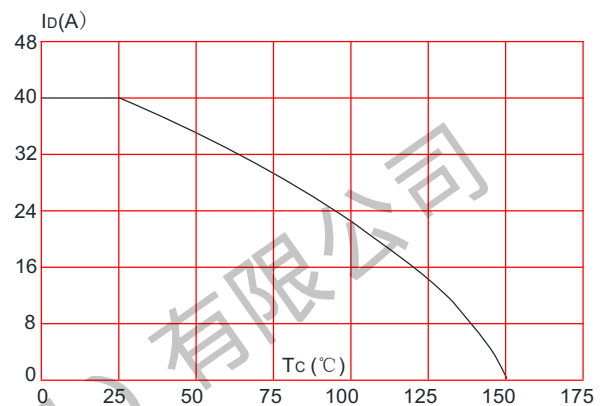
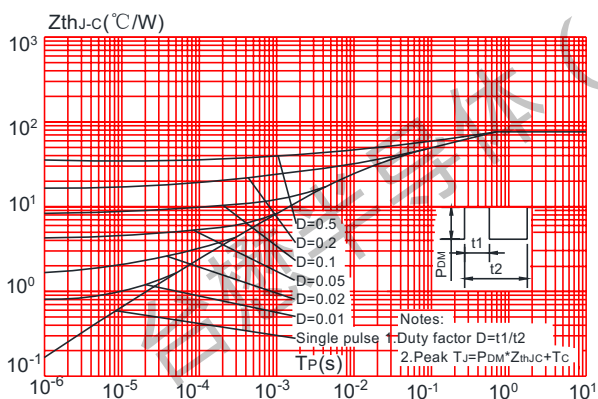


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Maximum Effective Transient Thermal Impedance, Junction-to-Case

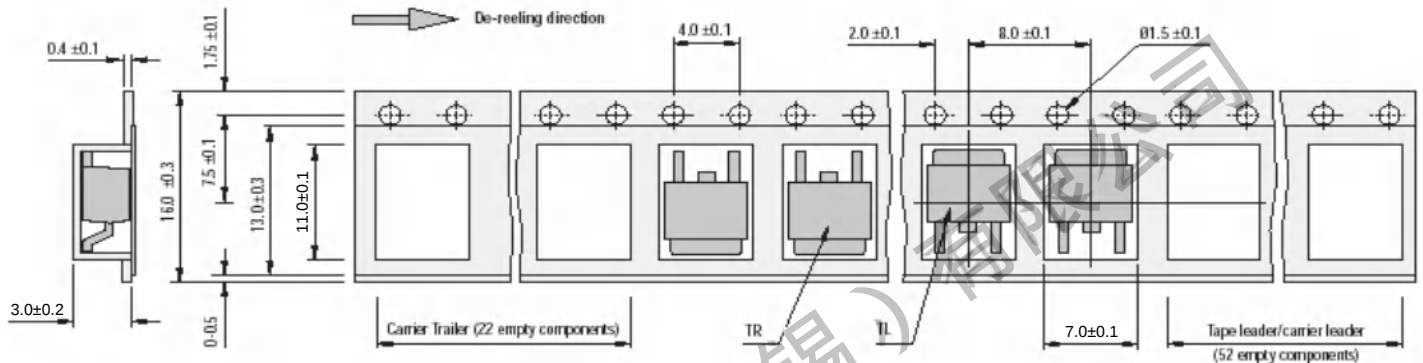




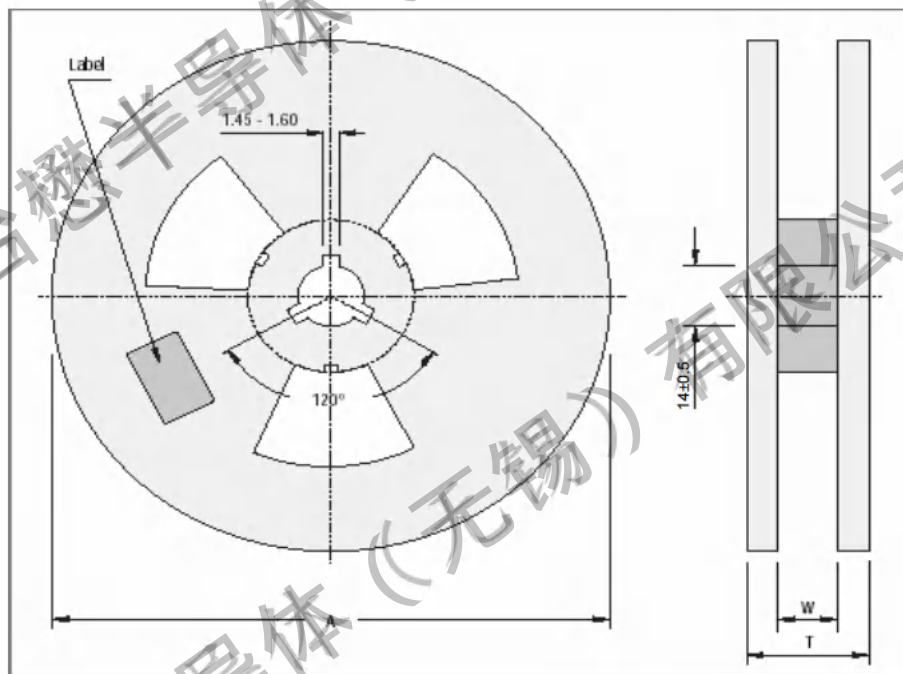
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TO-252-3L Embossed Carrier Tape



TO-252-3L Reel



All Dimensions are in mm

Reel Specifications				
Package	Tape Width	Reel Dia. A - Max	Inside Thickness W	Reel Thickness T - max
TO-252-3L	16	330	18.0 ± 1.5	20

Packaging Information

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13 inch	5,000 pcs	355×370×50	25,000 pcs	380×275×380	



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Revision history:

Date	Rev	Description	Page
2023.05.23	23.05	Original	